

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P07AS uses advanced trench technology and design to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge .This device is well suited for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -60V, I_{D} = -7A$

 $R_{DS(ON)}$ <65m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <85m Ω @ V_{GS} =-4.5V

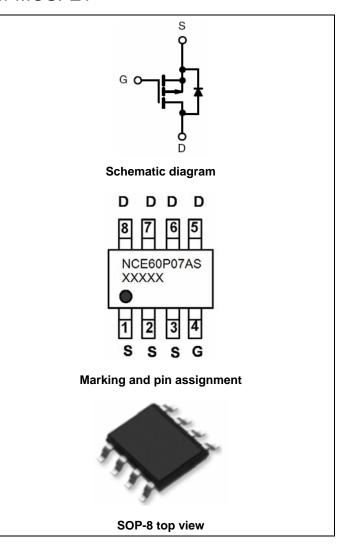
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Load switch
- PWM application

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P07AS	NCE60P07AS	SOP-8	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-7	А
Pulsed Drain Current	I _{DM}	-30	Α
Maximum Power Dissipation	P _D	3.0	W
Single pulse avalanche energy (Note 5)	E _{AS}	65	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{θJC}	41.7	°C/W
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	В	V _{GS} =-10V, I _D =-7A	-	55	65	mΩ
Diam-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-7A	-	65	85	mΩ
Forward Transconductance	g FS	V_{DS} =-5 V , I_{D} =-7 A	-	15	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ 20\/\/ 0\/	-	1108	-	PF
Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V, F=1.0MHz	-	73.7	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVITIZ	-	58.2	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, R_L =4.2 Ω ,	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_G =3 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q_g	V - 20 I - 7A	-	23.4	-	nC
Gate-Source Charge	Q_{gs}	V_{DS} =-30, I_{D} =-7A, V_{GS} =-10V	-	4.1	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	4.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS} =0 V , I_{S} =-7 A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-7	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = -7A$	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC

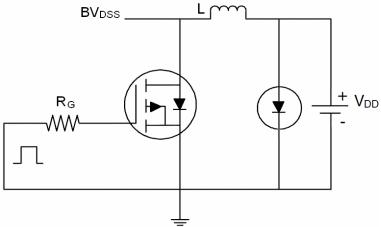
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

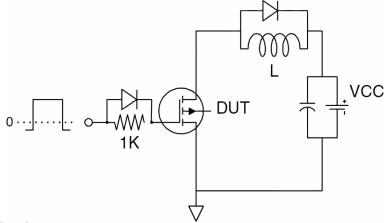


Test Circuit

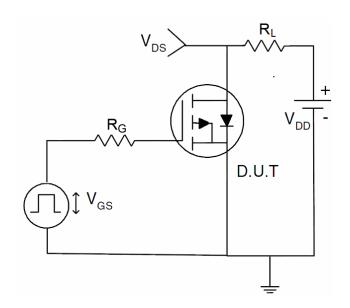
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

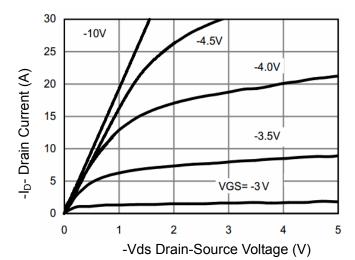


Figure 1 Output Characteristics

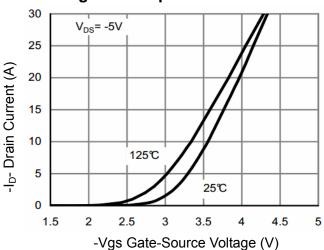
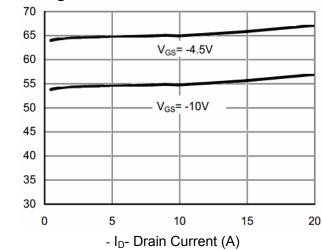


Figure 2 Transfer Characteristics



Rdson On-Resistance(m Ω)

Figure 3 Rdson- Drain Current

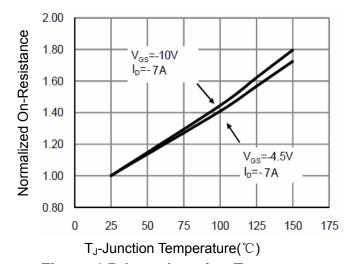
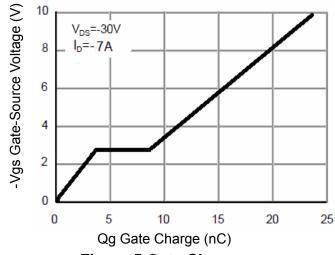


Figure 4 Rdson-Junction Temperature





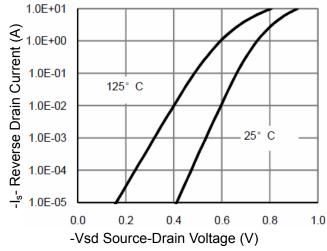


Figure 6 Source- Drain Diode Forward



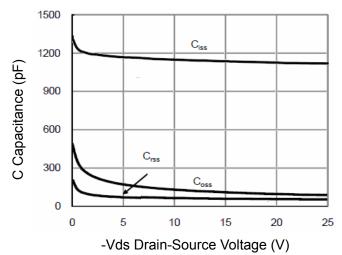
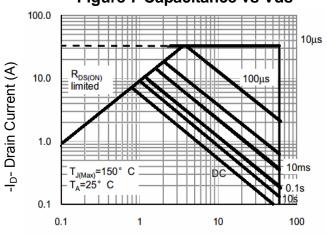
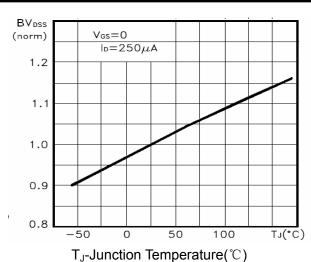


Figure 7 Capacitance vs Vds



-Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



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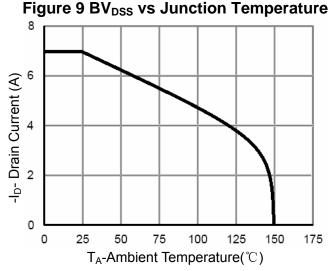


Figure 10 ID Current De-rating

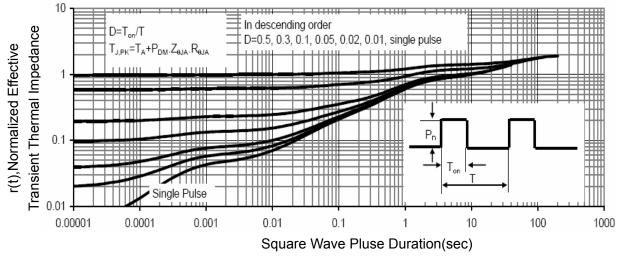
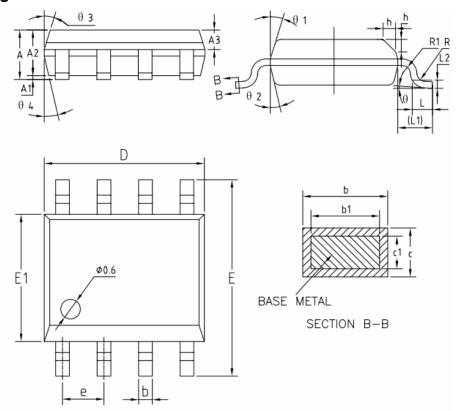


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX		
Α	1.35	1.55	1.75		
A1	0.10	0.15	0.25		
A2	1.25	1.40	1.65		
A3	0.50	0.60	0.70		
Ь	0.38	_	0.51		
b1	0.37	0.42	0.47		
С	0.18	_	0.25		
c1 D E	0.17	0.20	0.23		
D	4.80	4.90	5.00		
E	5.80	6.00	6.20		
E1	3.80	3.90	4.00		
е	1.17	1.27	1.37		
L L1	0.45	0.60	0.80		
L1		1.04REF			
L2	0.25BSC				
R	0.07	_	ı		
R1	0.07	_	_		
h	0.30	0.40	0.50		
θ	0.	_	8.		
θ 1	15 °	17*	19*		
θ 2	11*	13°	15 °		
θ 3	15 °	17*	19*		
θ 4	11*	13°	15 °		

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NCE60P07AS

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